

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A method for fabricating a semiconductor structure, comprising:
 - depositing a polysilicon layer on the semiconductor substrate;
 - removing a portion of the polysilicon layer to form a high region and a low region;
 - forming a silicide layer over the semiconductor substrate;
 - selecting chemical mechanical polishing parameters to remove the silicide layer at a first rate and to remove the polysilicon layer at a second rate, where the first rate is higher than the second rate; and
 - removing a portion of the silicide layer by chemical mechanical polishing at the first rate;
 - forming a dielectric layer over the silicide layer;
 - removing a portion of the dielectric layer to expose the portion of the silicide layer before removing the portion of the silicide layer; and
 - forming a top layer after forming the dielectric layer and removing a portion of the top layer before removing the portion of the dielectric layer, in which the top layer comprises a titanium nitride layer.
2. (Previously Presented) The method of claim 1, wherein the high region and the low region are formed before the silicide layer is formed and the portion of the silicide layer removed by chemical mechanical polishing is removed from the high region.
- 3-5. (Canceled)
6. (Currently Amended) The method of claim 5, wherein the dielectric layer comprises silicon dioxide.

7. (Currently Amended) The method of claim 5 1, wherein the dielectric layer comprises silicon nitride.

8. (Currently Amended) The method of claim 5 1, wherein the portion of the dielectric layer is removed by chemical mechanical polishing.

9-10. (Canceled)

11. (Currently Amended) The method of claim 10 1, wherein the portion of the titanium nitride layer is removed by chemical mechanical polishing.

12. (Currently Amended) The method of claim 11 1, wherein the portion of the titanium nitride layer is removed with a first slurry and the portion of the dielectric layer is removed with a second slurry.

13. (Previously Presented) The method of claim 12, wherein a polishing rate of the titanium nitride layer with the first slurry is greater than a polishing rate of the dielectric layer with the second slurry.

14. (Currently Amended) The method of claim 12, wherein a polishing rate of the titanium nitride layer with the second first slurry is less than a polishing rate of the dielectric layer with the second slurry.

15-22. (Canceled)